

No.2391

2SK771

N-Channel Junction Silicon FET

Low-Frequency General-Purpose Amp Applications

Applications

. Variable resistors, analog switches, AF amp, constant-current circuit

Features

- . Adoption of FBET process
- . Very small-sized package permitting sets to be made smaller and slimmer

Absolute Maximum Ratings at Ta:	=25 ⁰ C		unit
Drain to Source Voltage	$v_{ exttt{DSX}}$	40	V
Gate to Drain Voltage	VGDS	-40	V
Gate Current	I.	10	mA
Drain Current	$P_{\mathrm{D}}^{\mathrm{J}}$	20	mA
Allowable Power Dissipation	P_{D}	200	$\mathbf{m} \mathbf{W}$
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	оС

Electrical Characteristics at 'Gate to Drain Breakdown Voltage	-	I _G =-10µA, V _{DS} =0	min -40	typ	max	unit V
Gate Cutoff Current Cutoff Voltage Drain Current Forward Transfer Admittance Input Capacitance Reverse Transfer Capacitance Noise Figure	IDSS Yfs	$\begin{array}{l} v_{GS}\!=\!-20\text{V}, v_{DS}\!=\!0 \\ v_{DS}\!=\!10\text{V}, I_{D}\!=\!1\mu\text{A} \\ v_{DS}\!=\!10\text{V}, v_{GS}\!=\!0 \\ v_{DS}\!=\!10\text{V}, v_{GS}\!=\!0, f\!=\!1\text{kHz} \\ v_{DS}\!=\!10\text{V}, v_{GS}\!=\!0, f\!=\!1\text{MHz} \\ v_{DS}\!=\!10\text{V}, v_{GS}\!=\!0, f\!=\!1\text{MHz} \\ v_{DS}\!=\!10\text{V}, v_{GS}\!=\!1, f\!=\!1\text{V}, v_{GS}\!=\!1, f\!=\!1\text{MHz} \\ v_{DS}\!=\!10\text{V}, v_{GS}\!=\!1, f\!=\!1\text{V}, v_{GS}\!=\!1, f\!=\!1\text{V}, v_{GS}\!=\!1, f\!=\!1, f\!=$	-0.3 1.2* 4.5	_	12.0*	nA V mA mS pF pF dB

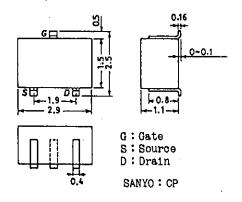
*: The 2SK771 is classified by IDSS as follows (unit:mA):

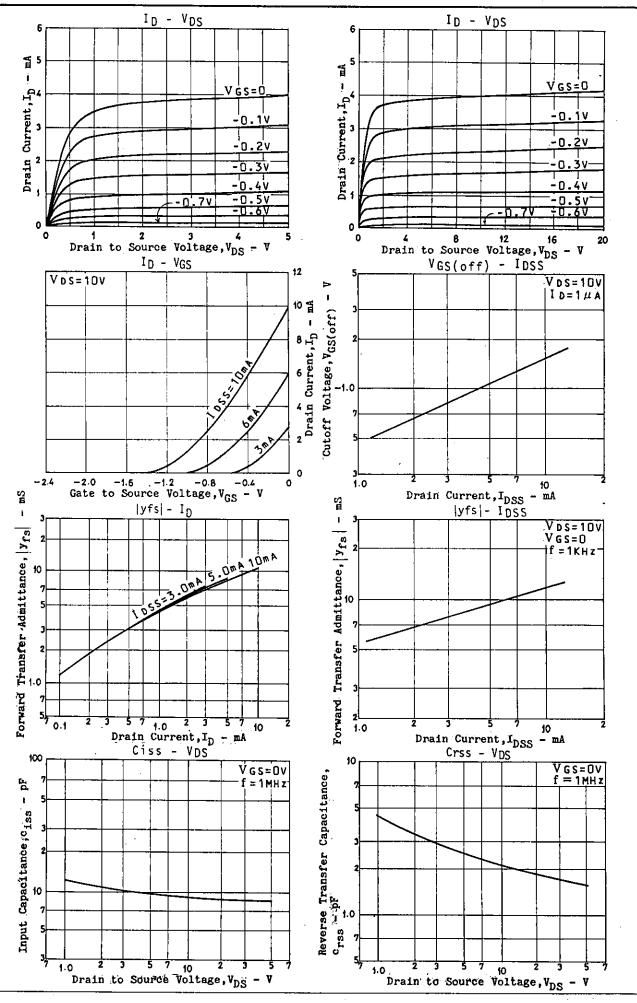
			<u> </u>		
1.2 3 3.0	2.5 4	6.0	5.0	5	12.0

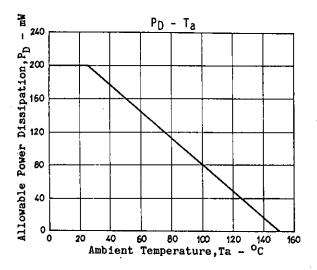
Marking : FJ

h_{FE} rank:3,4,5

Package Dimensions 2050 (unit:mm)







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